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Simulations of bar printing over a MOSFET device using i-line and deep-UV resists

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ABSTRACT

We presented numerical simulations of printing of a bar in photoresist over a MOSFET gate using positive and negative, I-line and deep-UV resists. The masks were chosen to produce the same nominal structure. The resist process was simulated in three separate phases: exposure, post-exposure bake, and development. Three-dimensional relief images of the printed bar are given for these cases.